

35A, 600V SUPER-FAST RECOVERY RECTIFIER

GENERAL DESCRIPTION

SFR35F60F2 is a Super-Fast Recovery Diode, fabricated in advanced silicon planar epitaxial technology. The process parameter and the device structure are fine tuned with optimized performance of forward voltage drop and reverse recovery time.

Accuracy epitaxial dope control, advanced planar junction terminal structure and the platinum doped life control, guarantee the best overall performance, ruggedness and reliability characteristics.

This device is intended for use in the output rectification stage of SMPS, UPS, DC-DC converters as well as free-wheeling diode in low voltage inverters and chopper motor drivers.

FEATURES

- Ultrafast 60 Nanosecond Recovery Time
- High Current Capability
- Low Forward Voltage Drop
- High surge current capability
- Low reverse current leakage
- 175°C Operating Junction Temperature

ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SFR35F60F2	TO-220F-2L	35F60F2	Pb free	Tube





ABSOLUTE MAXIMUM RATINGS

Characteristics	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	600	V
Average Rectified Forward Current	I _{F(AV)}	35	А
Peak Forward Surge Current @8.3ms	I _{FSM}	200	А
Power Dissipation(T _C =25°C)	PD	230	W
Single avalanche energy	EAS	100	mJ
Operation Junction Temperature Range	TJ	-40~+175	°C
Storage Temperature Range	T _{stg}	-40~+175	°C

THERMAL CHARACTERISTICS (PER LEG)

Characteristics	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{ ext{e}_{JC}}$			3.5	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Conditions	Min.	Тур.	Max.	Unit
	VF	I _F =30.0Amps, T _C =25°C		1.80	2.55	V
Maximum Forward Voltage		I _F =35.0Amps, T _C =25°C		1.85	2.60	V
Maximum Forward voltage		I _F =30.0Amps, T _C =125°C		1.40	2.05	V
		I _F =35.0Amps, T _C =125°C		1.45	2.2	V
Maximum Instantaneous	1	V _R = 600V, T _C =25°C			5.0	μA
Reverse Current	I _R	V _R = 600V, T _C =125°C			500	μA

SWITCH CHARACTERISTIC

Characteristics	Symbol	Conditions	Min.	Тур.	Max.	Unit
	т	$I_F=1A$, dIF/dt =100A/µs, $V_R=30V$		30		ns
Reverse Recovery Time	T _{RR}	I _F =30A, dIF/dt =100A/µs, V _R =30V		32		ns
Reverse Recovery Time	T _{RR}			60		ns
Reverse Recovery Current	I _{RRM}	I _F =30A, dIF/dt =200A/μs,V _R =390V,		3.2		А
Reverse Recovery Charge	Q _{RR}	T _c =25°C		90		nC



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TYPICAL CHARACTERISTICS





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PACKAGE OUTLINE





MOS DEVICES OPERATE NOTES:

Electrostatic charges may exist in many things. Please take following preventive measures to prevent effectively the MOS electric circuit as a result of the damage which is caused by discharge:

- The operator must put on wrist strap which should be earthed to against electrostatic. •
- Equipment cases should be earthed. •
- All tools used during assembly, including soldering tools and solder baths, must be earthed.
- MOS devices should be packed in antistatic/conductive containers for transportation.

UNIT: mm



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- 1. Silan reserves the right to make changes of this instruction without notice.
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- 8. Product promotion is endless, our company will wholeheartedly provide customers with better products!
- 9. Website: http://www.silan.com.cn



SFR35F60F2_Datasheet

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